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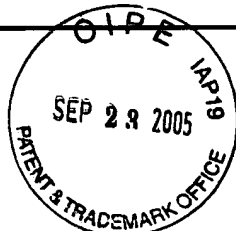
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Examiner

To Be Assigned

Group Art Unit

To Be AssignedInvention: **CHEMICALLY AMPLIFIED POSITIVE PHOTSENSITIVE RESIN COMPOSITION**I hereby certify that this **English Language abstract of JP 4-182650 - 2 Pages***(Identify type of correspondence)*

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(21)Application number : 02-312413 (71)Applicant : FUJI YAKUHI KOGYO KK

(22)Date of filing : 17.11.1990 (72)Inventor : IMAI KEN
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(54) POSITIVE TYPE PHOTSENSITIVE COMPOSITION AND FORMATION OF MICROLENS

(57)Abstract:

PURPOSE: To obtain accurate microlense having a high refractive index, heat, light and solvent resistance by using a chlorobenzaldehyde-diphenoxyethylacetal compd. and a specified compd.

CONSTITUTION: A soln. prepd. by dissolving 30 g cresol novolak resin, 10 g p-chlorobenzaldehyde-diphenoxyethylacetal and 0.25 g 2-(p-methoxy-phenyl)-4,6-bis(trichloromethyl)-s-triazine in 71 g ethylene glycol monoethyl acetate is filtered with a membrane filter to obtain a positive type resist soln. A glass sheet treated with hexamethyldi-silazane is spin-coated with the resist soln. and dried with a hot plate to obtain a resist layer. This layer is subjected to contact exposure with UV and developed by immersion in an aq. soln. of tetramethylammonium hydroxide having 2.38% concn. to form a resist pattern. Convex lenses are formed by heating the resist pattern to 100-160° C with a hot plate and then uniform exposure is carried out with 25 mj/cm² far UV.

LEGAL STATUS

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